PS21265-P/AP

TRANSFER-MOLD TYPE
INSULATED TYPE

PS21265

INTEGRATED POWER FUNCTIONS

600V/20A low-loss 5th generation IGBT inverter bridge for three phase DC-to-AC power conversion

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

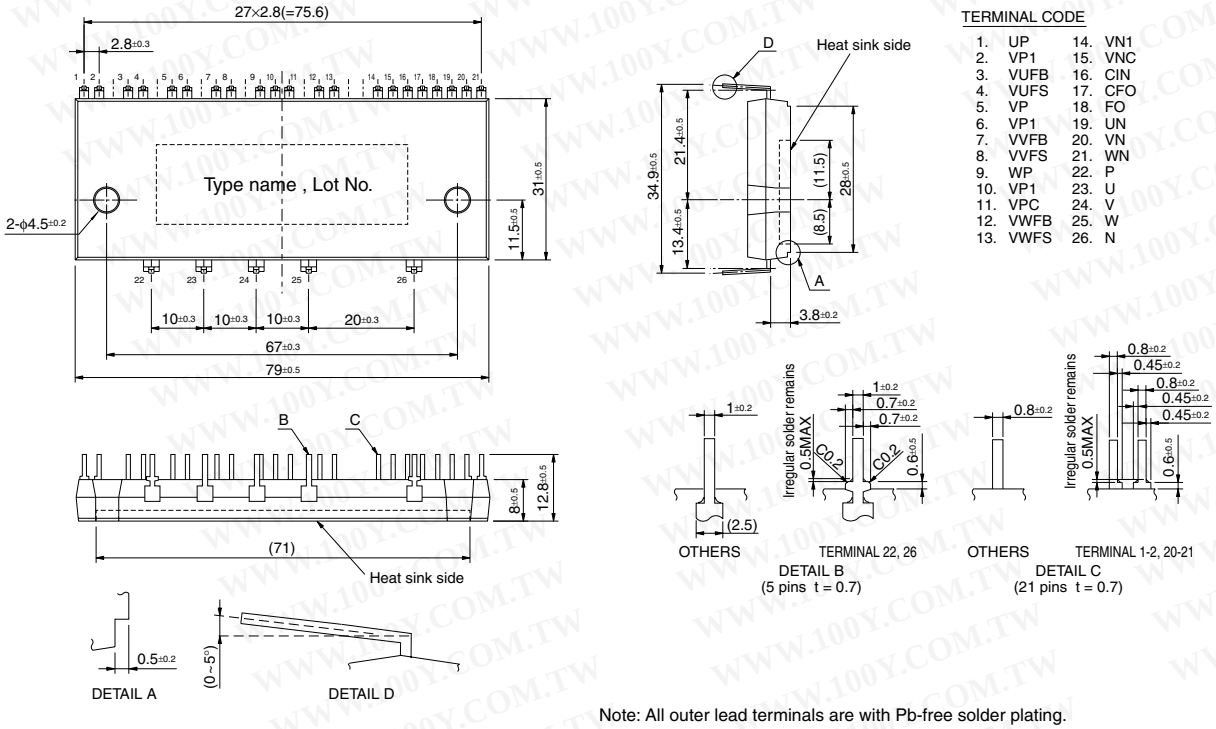
- For upper-leg IGBTs :Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection.
- For lower-leg IGBTs : Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC).
- Fault signaling : Corresponding to an SC fault (Lower-side IGBT) or a UV fault (Lower-side supply).
- Input interface : 3, 5V line compatible. (High Active)
- UL Approved : Yellow Card No. E80276

APPLICATION

AC100V~200V three-phase inverter drive for small power motor control.

Fig. 1 PACKAGE OUTLINES (Short-pin type : PS21265-P) Refer Fig. 6 for long-pin type : PS21265-AP.

Dimensions in mm



NOTE

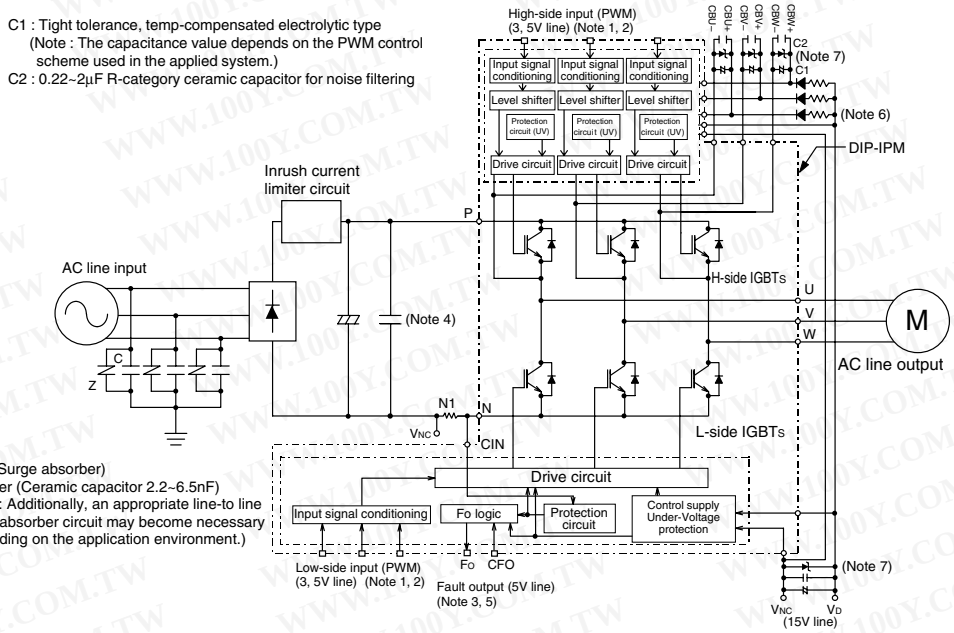
TERMINAL CODE

1.	UP	14.	VN1
2.	VP1	15.	VNC
3.	VUFB	16.	CIN
4.	VUFS	17.	CFO
5.	VP	18.	FO
6.	VP1	19.	UN
7.	VVFB	20.	VN
8.	VVFS	21.	WN
9.	WP	22.	P
10.	VP1	23.	U
11.	VPC	24.	V
12.	VWFB	25.	W
13.	VWFS	26.	N

Note: All outer lead terminals are with Pb-free solder plating.

MITSUBISHI ELECTRIC

Fig. 2 INTERNAL FUNCTIONS BLOCK DIAGRAM (TYPICAL APPLICATION EXAMPLE)



Note1: The logic of input signal is high-active. The DIP-IPM input signal section integrates a 2.5kΩ(min) pull-down resistor. If using external RC filter, pay attention to satisfy the turn-on/off threshold voltage requirement.

2: By virtue of integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible.

3: This output is open drain type. The signal line should be pulled up to the positive side of the 5V power supply with approximately 10kΩ resistor.

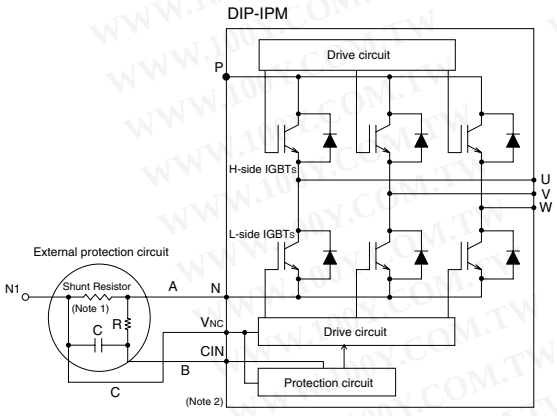
4: The wiring between the power DC link capacitor and the P, N1 terminals should be as short as possible to protect the DIP-IPM against catastrophic high surge voltages. For extra precaution, a small film type snubber capacitor (0.1~0.22μF, high voltage type) is recommended to be mounted close to these P & N1 DC power input pins.

5: Fo output pulse width should be decided by putting external capacitor between CFO and V_{NC} terminals. (Example : C_{FO}=22nF → t_{FO}=1.8ms (Typ.))

6: High voltage (600V or more) and fast recovery type (less than 100ns) diodes should be used in the bootstrap circuit.

7: To prevent ICs from surge destruction, it is recommended to insert a Zener diode (24V, 1W) between each control supply terminals.

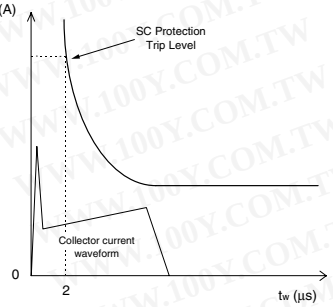
Fig. 3 EXTERNAL PART OF THE DIP-IPM PROTECTION CIRCUIT



Note1: In the recommended external protection circuit, please select the RC time constant in the range 1.5~2.0μs.

2: To prevent erroneous protection operation, the wiring of A, B, C should be as short as possible.

Short Circuit Protective Function (SC) :
SC protection is achieved by sensing the L-side DC-Bus current (through the external shunt resistor) after allowing a suitable filtering time (defined by the RC circuit). When the sensed shunt voltage exceeds the SC trip-level, all the L-side IGBTs are turned OFF and a fault signal (Fo) is output. Since the SC fault may be repetitive, it is recommended to stop the system when the Fo signal is received and check the fault.



MAXIMUM RATINGS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
V_{CC}	Supply voltage	Applied between P-N	450	V
$V_{CC(surge)}$	Supply voltage (surge)	Applied between P-N	500	V
V_{CES}	Collector-emitter voltage		600	V
±I_C	Each IGBT collector current	T_C = 25°C	20	A
±I_{CP}	Each IGBT collector current (peak)	T_C = 25°C, less than 1ms	40	A
P_C	Collector dissipation	T_C = 25°C, per 1 chip	51.2	W
T_j	Junction temperature	(Note 1)	–20~+125	°C

Note 1 : The maximum junction temperature rating of the power chips integrated within the DIP-IPM is 150°C (@ $T_C \leq$ 100°C) however, to insure safe operation of the DIP-IPM, the average junction temperature should be limited to $T_{j(ave)} \leq$ 125°C (@ $T_C \leq$ 100°C).

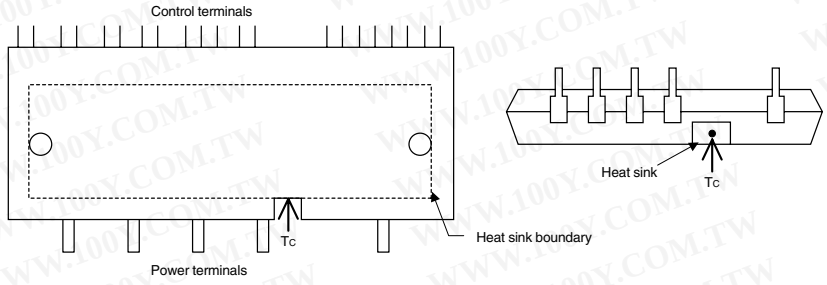
CONTROL (PROTECTION) PART

Symbol	Parameter	Condition	Ratings	Unit
V_D	Control supply voltage	Applied between V_{P1}-V_{PC}, V_{N1}-V_{NC}	20	V
V_{DB}	Control supply voltage	Applied between V_{UFB}-V_{UFS}, V_{VFB}-V_{VFS}, V_{WFB}-V_{WFS}	20	V
V_{IN}	Input voltage	Applied between U_P, V_P, W_P-V_{PC}, U_N, V_N, W_N-V_{NC}	–0.5~V_D+0.5	V
V_{FO}	Fault output supply voltage	Applied between F_O-V_{NC}	–0.5~V_D+0.5	V
I_{FO}	Fault output current	Sink current at F_O terminal	1	mA
V_{SC}	Current sensing input voltage	Applied between CIN-V_{NC}	–0.5~V_D+0.5	V

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
$V_{CC(PROT)}$	Self protection supply voltage limit (short circuit protection capability)	V_D = 13.5~16.5V, Inverter part T_j = 125°C, non-repetitive, less than 2 μs	400	V
T_C	Module case operation temperature	(Note 2)	–20~+100	°C
T_{stg}	Storage temperature		–40~+125	°C
V_{iso}	Isolation voltage	60Hz, Sinusoidal, AC 1 minute, connecting pins to heat-sink plate	2500	V_{rms}

Note 2 : T_C measurement point



THERMAL RESISTANCE

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Junction to case thermal resistance (Note 3)	Inverter IGBT part (per 1/6 module)	—	—	1.95	°C/W
$R_{th(j-c)F}$		Inverter FWDi part (per 1/6 module)	—	—	3.00	°C/W
$R_{th(c-f)F}$	Contact thermal resistance	Case to fin (per 1 module) thermal grease applied	—	—	0.067	°C/W

Note 3 : Grease with good thermal conductivity should be applied evenly with a thickness of about +100μm~+200μm on the contact surface of DIP-IPM and heat-sink.

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition		Limits			Unit
				Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_D = V_{DB} = 15V, V_{IN} = 5V	I_C = 20A, T_j = 25°C	—	1.55	2.05	V
			I_C = 20A, T_j = 125°C	—	1.65	2.15	
V_{EC}	FWDi forward voltage	T_j = 25°C, –I_C = 20A, V_{IN} = 0V		—	1.50	2.00	V
t_{on}	Switching times	V_{CC} = 300V, V_D = V_{DB} = 15V, I_C = 20A, T_j = 125°C, V_{IN} = 0 ↔ 5V, Inductive load (upper-lower arm)		0.65	1.25	1.85	μs
t_{rr}				—	0.30	—	μs
$t_{c(on)}$				—	0.40	0.60	μs
t_{off}				—	1.50	2.10	μs
$t_{c(off)}$				—	0.50	0.80	μs
I_{CES}	Collector-emitter cut-off current	V_{CE} = V_{CES}	T_j = 25°C	—	—	1	mA
			T_j = 125°C	—	—	10	

CONTROL (PROTECTION) PART

Symbol	Parameter	Condition		Limits			Unit
				Min.	Typ.	Max.	
I_D	Circuit current	V_D = V_{DB} = 15V, V_{IN} = 5V	Total of V_{P1}-V_{PC}, V_{N1}-V_{NC}	—	—	7.00	mA
			V_{UFB}-V_{UFS}, V_{VFB}-V_{VFS}, V_{WFB}-V_{WFS}	—	—	0.55	mA
		V_D = V_{DB} = 15V, V_{IN} = 0V	Total of V_{P1}-V_{PC}, V_{N1}-V_{NC}	—	—	7.00	mA
			V_{UFB}-V_{UFS}, V_{VFB}-V_{VFS}, V_{WFB}-V_{WFS}	—	—	0.55	mA
V_{FOH}	Fault output voltage	V_{SC} = 0V, FO circuit pull-up to 5V with 10kΩ		4.9	—	—	V
V_{FOL}		V_{SC} = 1V, I_{FO} = 1mA		—	—	0.95	V
$V_{SC(ref)}$	Short circuit trip level	T_C = –20~100°C, V_D = 15V (Note 4)		0.45	—	0.52	V
I_{IN}	Input current	V_{IN} = 5V		1.0	1.5	2.0	mA
UV_{DBt}	Control supply under-voltage protection	T_j ≤ 125°C	Trip level	10.0	—	12.0	V
UV_{DBr}			Reset level	10.5	—	12.5	V
UV_{Dt}			Trip level	10.3	—	12.5	V
UV_{Dr}			Reset level	10.8	—	13.0	V
t_{FO}	Fault output pulse width	C_{FO} = 22nF (Note 5)		1.0	1.8	—	ms
$V_{th(on)}$	ON threshold voltage	Applied between U_P, V_P, W_P-V_{PC}, U_N, V_N, W_N-V_{NC}		2.1	2.3	2.6	V
$V_{th(off)}$	OFF threshold voltage			0.8	1.4	2.1	V

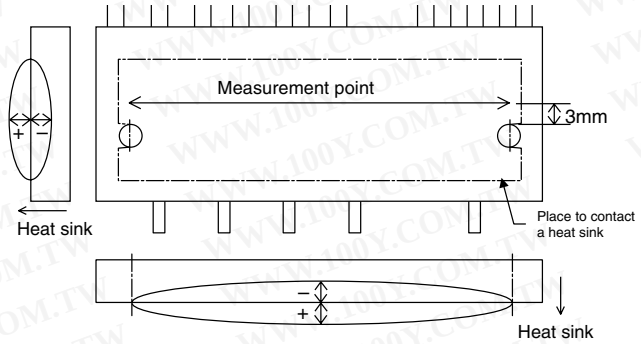
Note 4 : Short circuit protection is functioning only at the low-arms. Please select the external shunt resistance such that the SC trip-level is less than 2.0 times of the collector current rating (20A).

5 : Fault signal is output when the low-arms short circuit or control supply under-voltage protective functions operate. The fault output pulse-width t_{FO} depends on the capacitance value of C_{FO} according to the following approximate equation : $C_{FO} = 12.2 \times 10^{-6} \times t_{FO}$ [F].

MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Condition		Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	Mounting screw : M4	Recommended : 1.18 N·m	0.98	—	1.47	N·m
Weight			—	54	—	g
Heat-sink flatness		(Note 6)	–50	—	100	μm

Note 6 :

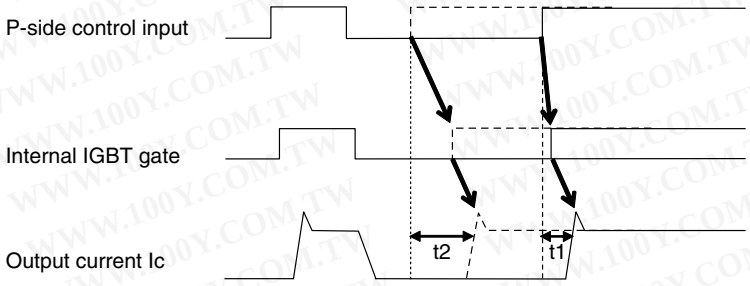


RECOMMENDED OPERATION CONDITIONS

Symbol	Parameter	Condition		Recommended value			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply voltage	Applied between P-N		0	300	400	V
V_D	Control supply voltage	Applied between V_{P1}-V_{PC}, V_{N1}-V_{NC}		13.5	15.0	16.5	V
V_{DB}	Control supply voltage	Applied between V_{UFB}-V_{UFS}, V_{VFB}-V_{VFS}, V_{WFB}-V_{WFS}		13.0	15.0	18.5	V
ΔV_D, ΔV_{DB}	Control supply variation			–1	—	1	V/μs
t_{dead}	Arm shoot-through blocking time	For each input signal, $T_C \leq 100°C$		2	—	—	μs
f_{PWM}	PWM input frequency	$T_C \leq 100°C$, $T_j \leq 125°C$		—	—	20	kHz
I_O	Allowable r.m.s. current	V_{CC} = 300V, V_D = V_{DB} = 15V, P.F = 0.8, sinusoidal PWM $T_C \leq 100°C$, $T_j \leq 125°C$ (Note 7)	f_{PWM} = 5kHz	—	—	14.0	Arms
			f_{PWM} = 15kHz	—	—	9.5	
PWIN(on)	Minimum input pulse width	(Note 8)		0.3	—	—	μs
PWIN(off)		200 ≤ V_{CC} ≤ 350V, 13.5 ≤ V_D ≤ 16.5V, 13.0 ≤ V_{DB} ≤ 18.5V, –20°C ≤ T_C ≤ 100°C, N-line wiring inductance less than 10nH (Note 9)	Below rated current	1.4	—	—	
			Between rated current and 1.7 times of rated current	2.5	—	—	
			Between 1.7 times and 2.0 times of rated current	3.0	—	—	
V_{NC}	V_{NC} variation	between V_{NC}-N (including surge)		–5.0	—	5.0	V

Note 7 : The Allowable r.m.s. current value depends on the actual application conditions.
8 : Input signal with ON pulse width less than PWIN(on) might make no response.
9 : IPM might make no response or response delay to next turn-on pulse if off-pulse width is less than PWIN(off). (Please refer to Fig. 4)
Please refer to Fig. 9 for recommended wiring method too.

Fig. 4 CURRENT OUTPUT WHEN INPUT SIGNAL IS LESS THAN ALLOWABLE MINIMUM INPUT PULSE WIDTH PWIN(off) (P-side only)



Real line ··· off pulse width > PWIN(off) ; turn on time t1
Broken line ··· off pulse width < PWIN(off) ; turn on time t2

Fig. 5 THE DIP-IPM INTERNAL CIRCUIT

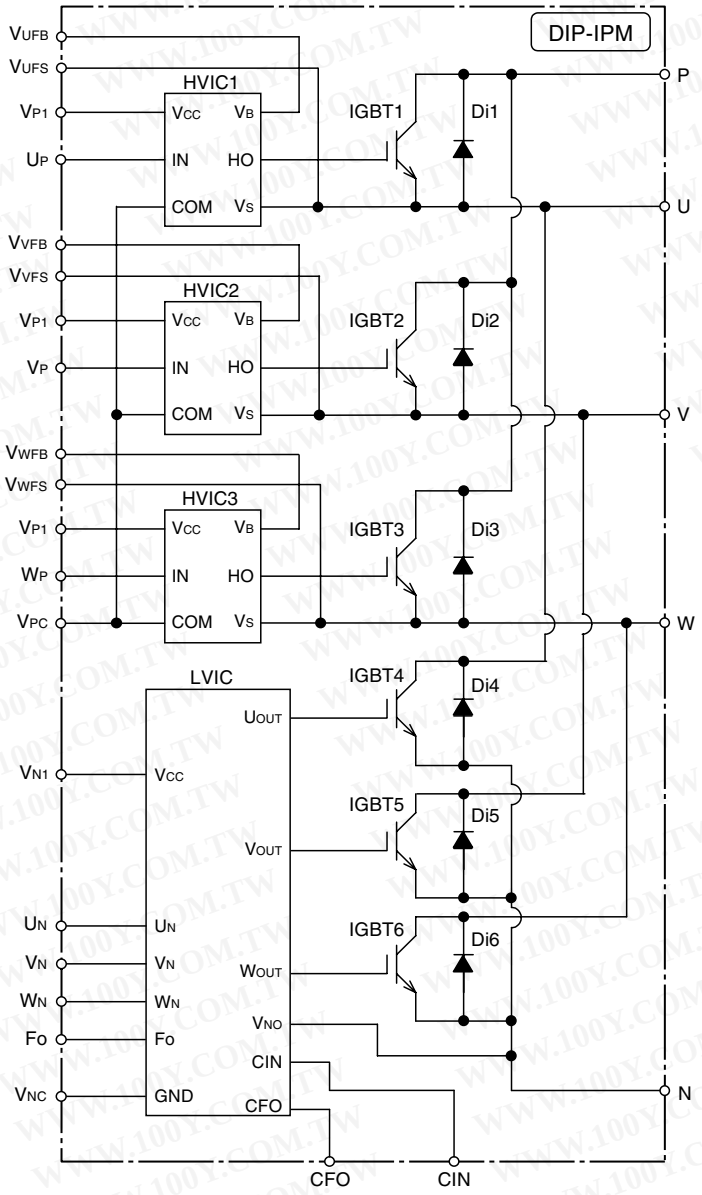


Fig. 6 PACKAGE OUTLINES (Long-pin type : PS21265-AP)

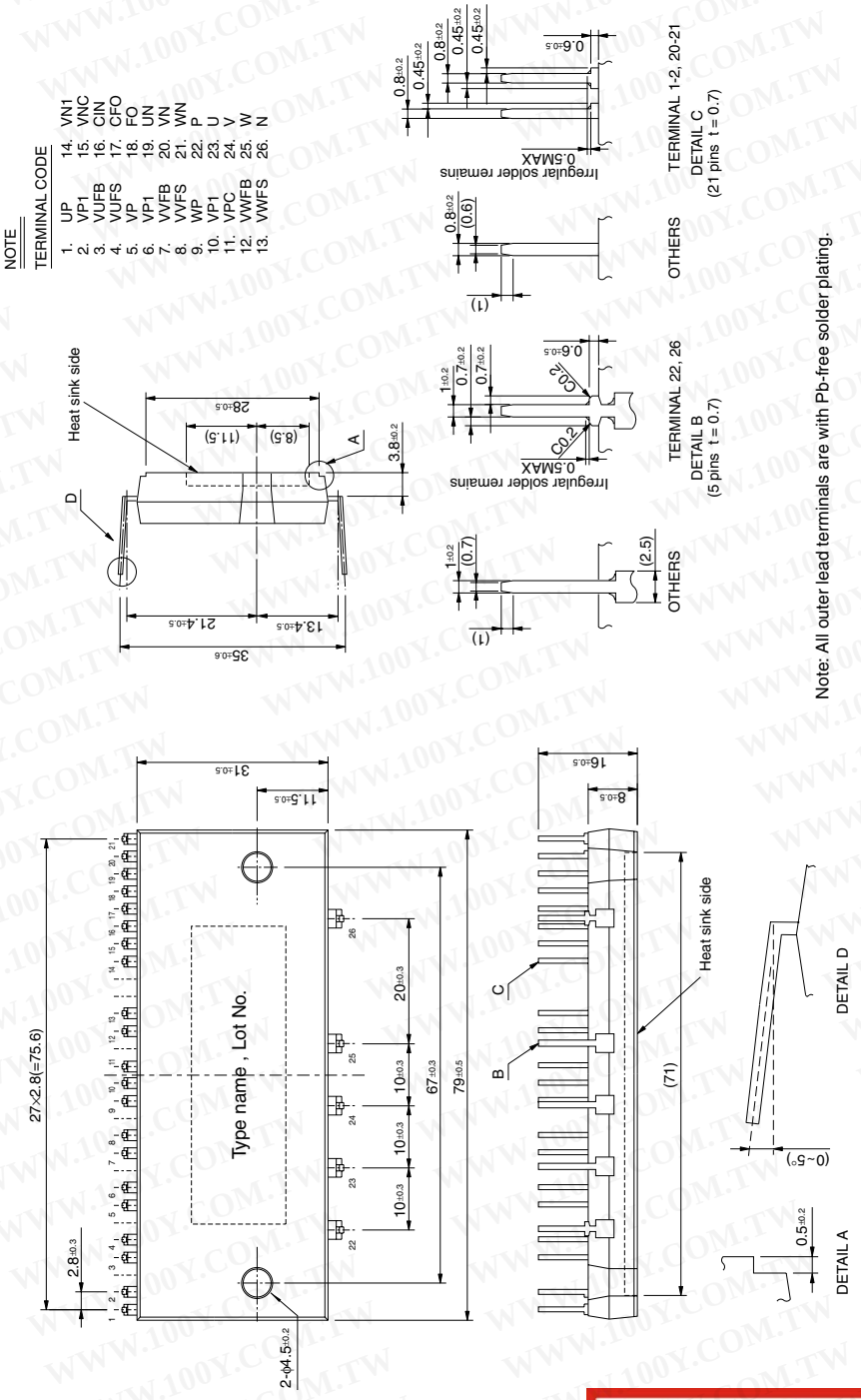
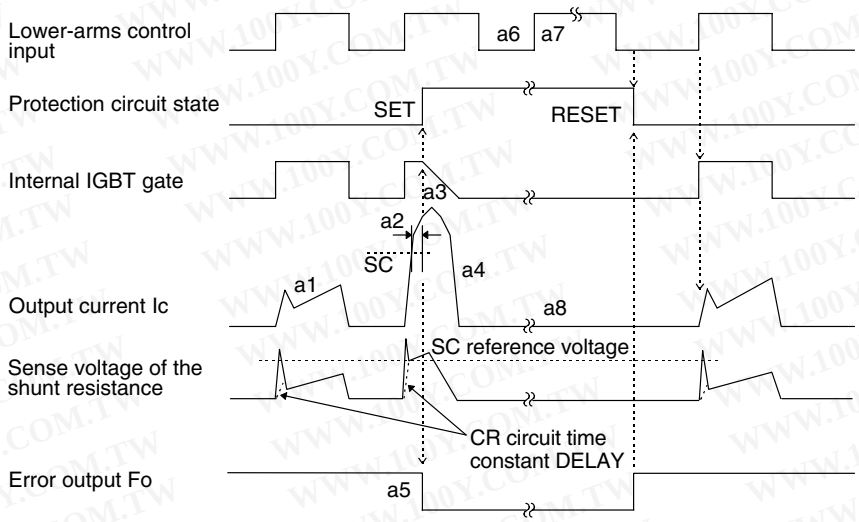


Fig. 7 TIMING CHARTS OF THE DIP-IPM PROTECTIVE FUNCTIONS

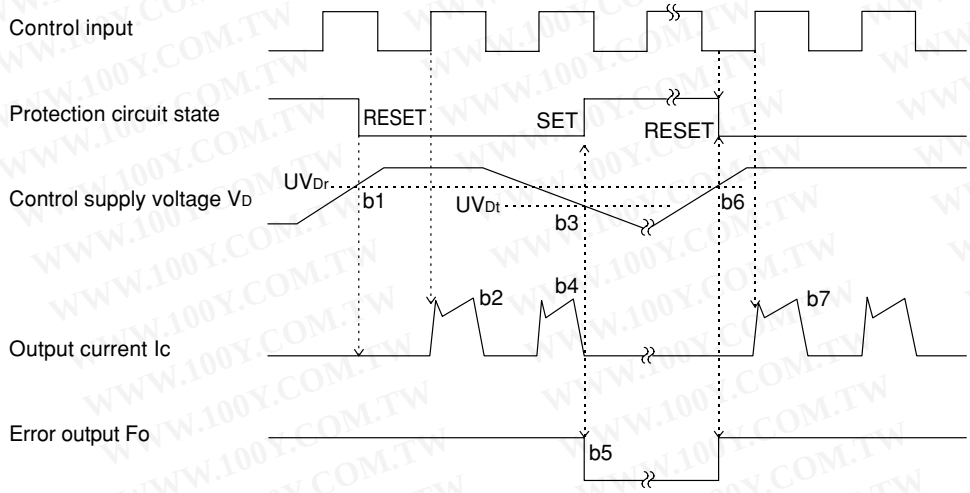
[A] Short-Circuit Protection (Lower-arms only) (with external shunt resistor and CR connection)

a1. Normal operation : IGBT ON and carrying current.
a2. Short circuit current detection (SC trigger).
a3. Hard IGBT gate interrupt.
a4. IGBT turns OFF.
a5. FO timer operation starts : The pulse width of the FO signal is set by the external capacitor CFO.
a6. Input "L" : IGBT OFF state.
a7. Input "H" : IGBT ON state, but during the FO signal active period the IGBT doesn't turn ON.
a8. IGBT OFF in spite of "H" input.



[B] Under-Voltage Protection (Lower-arm, UVD)

b1. Control supply voltage rises : After the voltage reaches UVDr level, the circuits start to operate when the next input is applied.
b2. Normal operation : IGBT ON and carrying current.
b3. Under voltage trip (UVDt).
b4. IGBT OFF in spite of control input condition.
b5. FO operation starts. The minimum pulse width of FO is set by the external capacitor CFO, and FO outputs continuously during UV period.
b6. Under voltage reset (UVDr).
b7. Normal operation : IGBT ON and carrying current.



[C] Under-Voltage Protection (Upper-arm, UV_{DB})

c1. Control supply voltage rises : Operation starts soon after UV_{DBr}.
c2. Normal operation : IGBT ON and carrying current.
c3. Under voltage trip (UV_{DBt}).
c4. IGBT OFF in spite of control input condition, but there is no Fo signal output.
c5. Under voltage reset (UV_{DBr}).
c6. Normal operation : IGBT ON and carrying current.

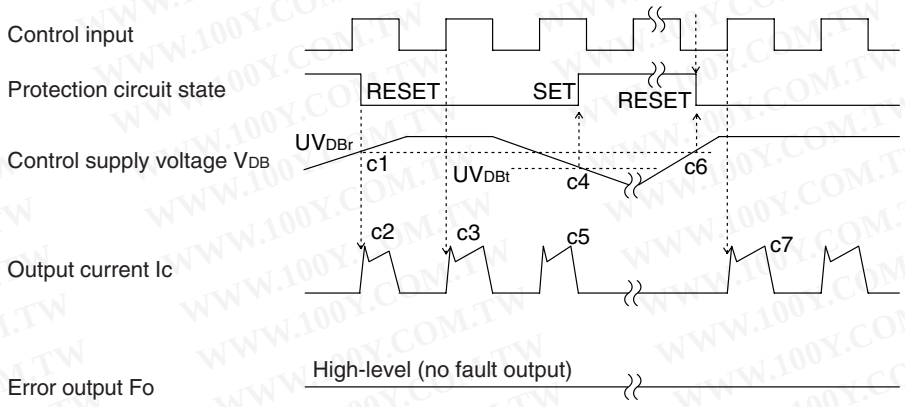
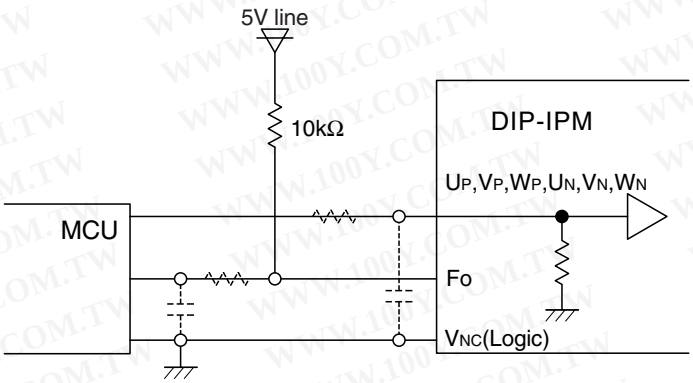


Fig. 8 RECOMMENDED MCU I/O INTERFACE CIRCUIT



Note : RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board.
The DIP-IPM input signal section integrates a 2.5kΩ(min) pull-down resistor. Therefore, if using external RC filter, pay attention to satisfy the turn-on/off threshold voltage requirement.

Fig. 9 RECOMMENDED WIRING OF SHUNT RESISTOR

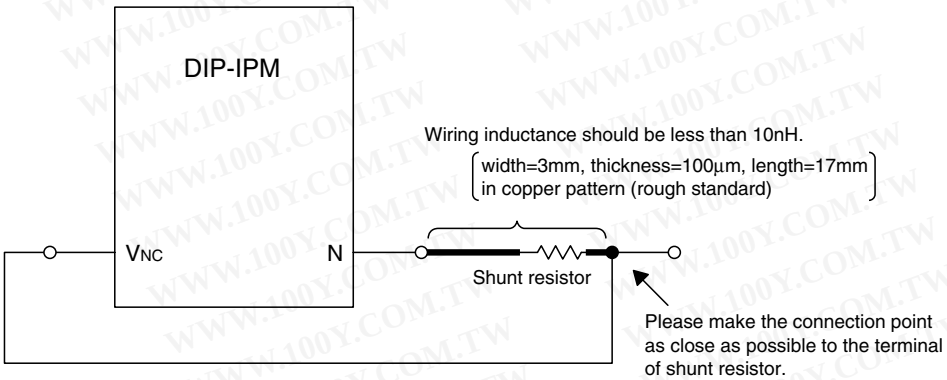
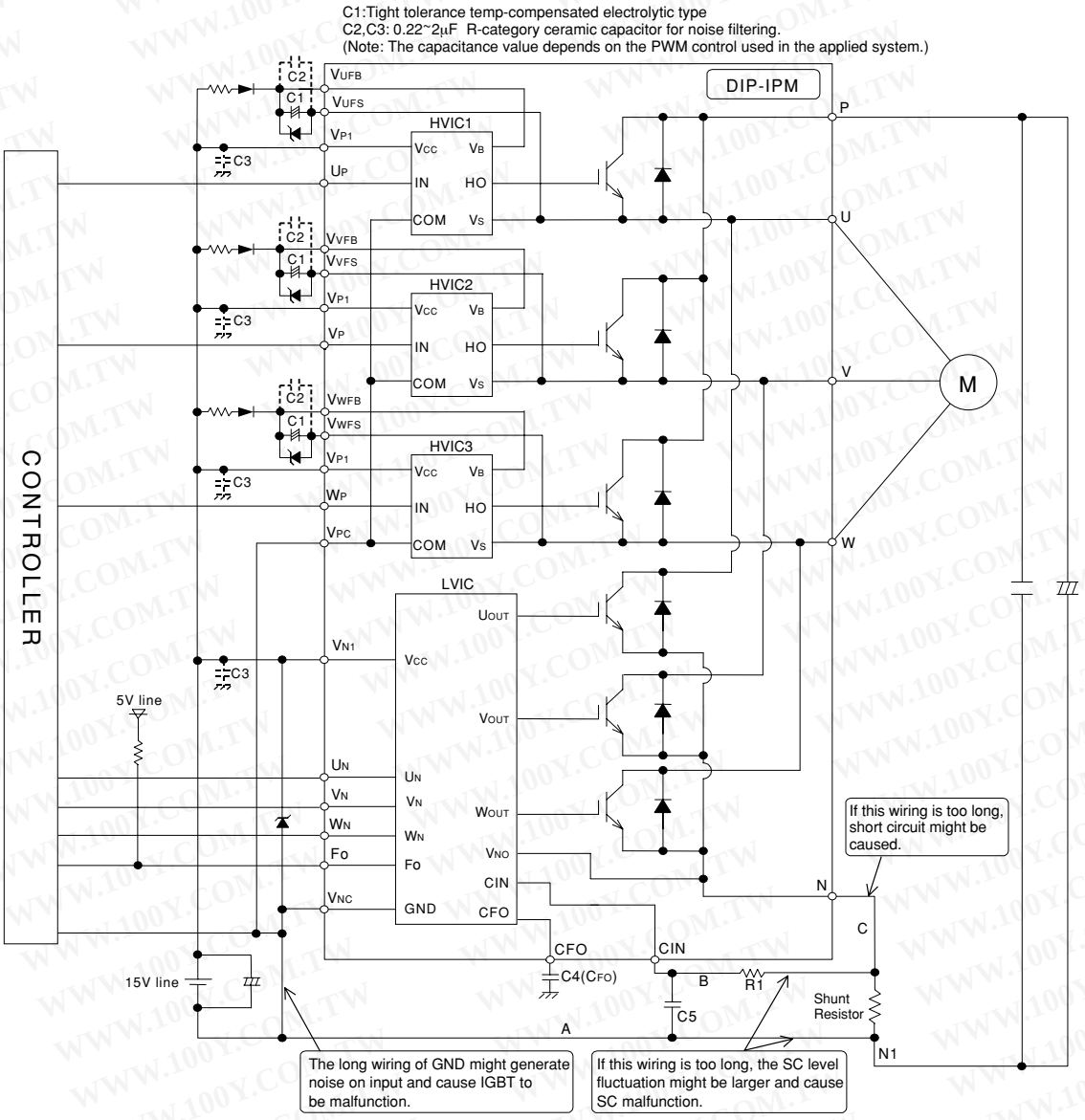


Fig. 10 EXAMPLE OF TYPICAL DIP-IPM APPLICATION CIRCUIT



Note 1 : To prevent the input signals oscillation, the wiring of each input should be as short as possible. (Less than 2-3cm)

2 : By virtue of integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible.

3 : F_O output is open drain type. This signal line should be pulled up to the positive side of the 5V power supply with approximately 10kΩ resistor.

4 : F_O output pulse width is determined by the external capacitor between CFO and V_{NC} terminals (C_{FO}). (Example : C_{FO} = 22nF → t_{FO} = 1.8ms (typ.))

5 : The logic of input signal is high-active. The DIP-IPM input signal section integrates a 2.5kΩ (min) pull-down resistor. If using external RC filter, pay attention to satisfy the turn-on/off threshold voltage requirement.

6 : To prevent malfunction of protection, the wiring of A, B, C should be as short as possible.

7 : Please set the R1C5 time constant in the range 1.5~2μs.

8 : Each capacitor should be located as nearby the pins of the DIP-IPM as possible.

9 : To prevent surge destruction, the wiring between the smoothing capacitor and the P, N1 pins should be as short as possible. Approximately a 0.1~0.22μF snubber capacitor between the P-N1 pins is recommended.

10 : To prevent I_{CS} from surge destruction, it is recommended to insert a Zener diode (24V, 1W) between each control supply terminals.